



160V NPN SMALL SIGNAL TRANSISTOR IN SOT23

Description

This bipolar junction transistor (BJT) is designed to meet the stringent requirements of automotive applications.

Features

- BV_{CEO} > 160V
- Ideal for Low Power Amplification and Switching
- Complementary PNP Type Available (MMBT5401)
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen- and Antimony-Free. "Green" Device (Note 3)
- The MMBT5551Q is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

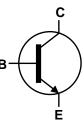
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Plated Leads Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.008 grams (Approximate)

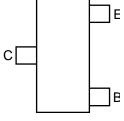
SOT23







Device Symbol



Top View Pin-Out

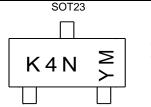
Ordering Information (Note 4)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
MMBT5551Q-7	K4N	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



K4N = Product Type Marking Code

YM = Date Code Marking

Y = Year (ex: H = 2020)

M = Month (ex: 9 = September)

Date Code Key

Year	2020	2021	20)22	2023	2024	2025	2026	5 20	27	2028	2029
Code	Н	ı		J	K	L	М	N	()	Р	R
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Absolute Maximum Ratings (@ T_A = +25°C unless otherwise specified)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	180	V
Collector-Emitter Voltage	V _{CEO}	160	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Continuous Collector Current (Note 5)	Ic	600	mA

Thermal Characteristics (@ $T_A = +25$ °C unless otherwise specified)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 5)	P_{D}	300	mW
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	417	°C/W	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C	

ESD Ratings (Note 6)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

- 5. For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- conditions whilst operating in a steady-state.

 6. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

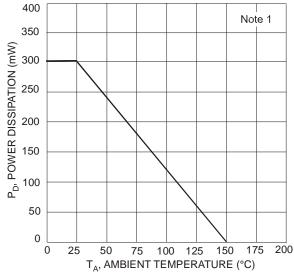


Fig. 1 Power Dissipation vs. Ambient Temperature



Electrical Characteristics @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)						
Collector-Base Breakdown Voltage	BV _{CBO}	180		V	$I_C = 100 \mu A, I_E = 0$	
Collector-Emitter Breakdown Voltage	BV _{CEO}	160		V	$I_C = 1.0 \text{mA}, I_B = 0$	
Emitter-Base Breakdown Voltage	BV _{EBO}	6.0		V	$I_E = 10\mu A, I_C = 0$	
Collector Cutoff Current	I _{CBO}	_	50	nΑ μΑ	V _{CB} = 120V, I _E = 0 V _{CB} = 120V, I _E = 0, T _A = 100°C	
Emitter Cutoff Current	I _{EBO}	_	50	nA	$V_{EB} = 4.0V, I_{C} = 0$	
ON CHARACTERISTICS (Note 7)	,	l.			, 25	
		80	_		$I_C = 1.0 \text{mA}, V_{CE} = 5.0 \text{V}$	
DC Current Gain	h _{FE}	80	250	_	$I_C = 10mA, V_{CE} = 5.0V$	
		30			$I_C = 50 \text{mA}, V_{CE} = 5.0 \text{V}$	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	_	0.15 0.20	٧	$I_C = 10mA$, $I_B = 1.0mA$	
Collector-Emilier Saturation voltage					$I_C = 50 \text{mA}, I_B = 5.0 \text{mA}$	
Base-Emitter Saturation Voltage	V-=()		1.0	V	$I_C = 10mA$, $I_B = 1.0mA$	
Dase-Emiller Saldration Voltage	V _{BE(sat)}		1.0	V	$I_C = 50 \text{mA}, I_B = 5.0 \text{mA}$	
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C_{obo}	_	6.0	pF	$V_{CB} = 10V$, $f = 1.0MHz$, $I_{E} = 0$	
Small Signal Current Gain	h _{fe}	50	250	_	$V_{CE} = 10V, I_{C} = 1.0mA,$ f = 1.0kHz	
Current Gain-Bandwidth Product	ft	100	300	MHz	V _{CE} = 10V, I _C = 10mA, f = 100MHz	
Noise Figure	nf	_	8.0	dB	$V_{CE} = 5.0V$, $I_{C} = 200\mu A$, $R_{S} = 1.0k\Omega$, $f = 1.0kHz$	

Notes: 7. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics (@ TA = +25°C, unless otherwise specified.)

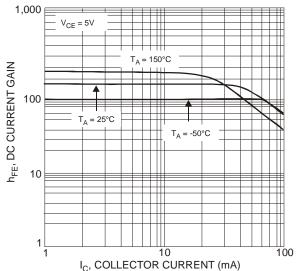
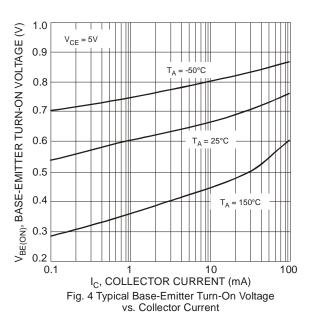


Fig. 2 Typical DC Current Gain vs. Collector Current



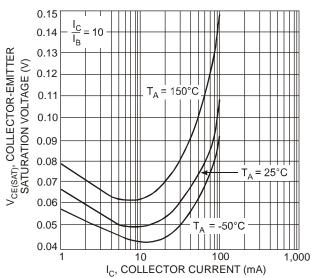


Fig. 3 Typical Collector-Emitter Saturation Voltage vs. Collector Current

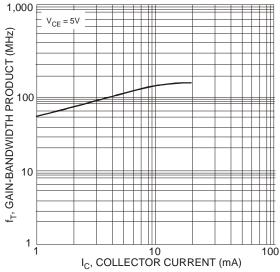
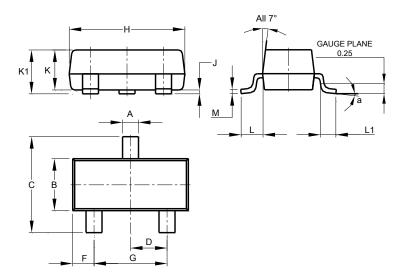


Fig. 5 Typical Gain-Bandwidth Product vs. Collector Current



Package Outline Dimensions

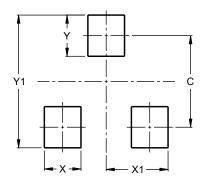
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
M	0.085	0.150	0.110				
а	0°	8°					
All	All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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